

**REMARKS**

Claims 1-21 are pending in the application. Although the Examiner has withdrawn consideration of the non-elected species, Applicants submit that since the generic claim 1 is considered allowable, that claims 2-4, 14-16 and 18-21 should be brought back into consideration in the present application.

Claim 18 is amended herein to correct a typographical error. Specifically, in line 7 of claim 18, the silicon nitride layer was originally recited as being deposited on the "tunnel" oxide layer. There was no antecedent basis for this term, since the claim included formation of a bottom oxide layer, not a tunnel oxide layer. Thus, the term "tunnel" has been replaced with the term "bottom". A version of claim 18 in which this correction is shown is provided in the attached Appendix, and the corrected version of claim 18 is set forth in the claims 1-21 shown in the Appeal Brief.

**Conclusion**

For all the foregoing reasons, Appellants respectfully submit that the present application is in condition for allowance, and respectfully request notice to such effect.

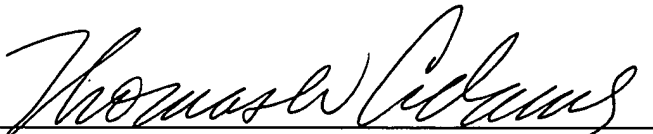
If the Examiner considers that a telephone interview would be helpful to facilitate favorable prosecution of this application, the Examiner is invited to telephone the undersigned.

It is believed no fee is required for this filing. However, if a fee is required, please charge the fee to Deposit Account No. 18-0988, Order No. AF01120.

Respectfully submitted,

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**APPENDIX**

Claim 18 as shown above has been amended as follows:

18. (Amended) A process for fabrication of a semiconductor device, the device including a floating gate FLASH structure comprising an ONO structure, comprising forming the ONO structure by:

- providing a semiconductor substrate having a floating gate electrode;
- forming a bottom oxide layer overlying the floating gate electrode by in-situ steam generation oxidation of a portion of a surface of the floating gate electrode;
- depositing a silicon nitride layer overlying the ~~tunnel~~ bottom oxide layer; and
- forming a top oxide layer overlying the silicon nitride layer by in-situ steam generation oxidation of a portion of the silicon nitride layer.